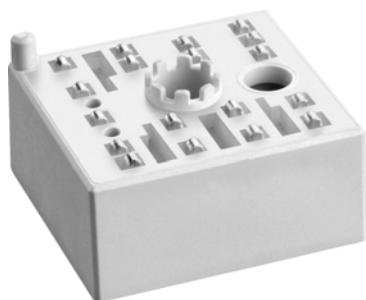


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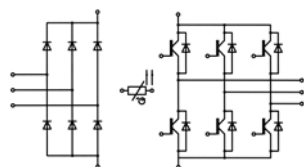
SKiIP 03NAC12T4V1

Features

- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- Temperature sensor: No basic insulation to main circuit, max. potential difference 850V to -DC

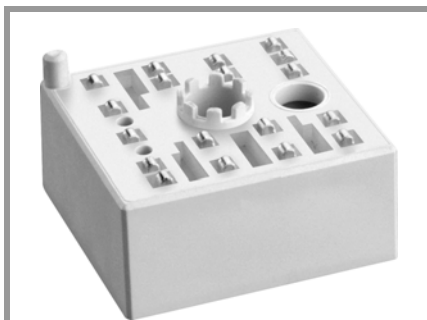


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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_{Cnom}			8	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		24	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
	$V_{GE} \leq 15\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
T_j			-40 ... 175	$^\circ\text{C}$
Inverse - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1200	V
I_F	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	9	A
		$T_s = 70^\circ\text{C}$	9	A
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	9	A
		$T_s = 70^\circ\text{C}$	9	A
I_{Fnom}			8	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		24	A
I_{FSM}	$t_p = 10\text{ ms}, \sin 180^\circ, T_j = 150^\circ\text{C}$		36	A
T_j			-40 ... 175	$^\circ\text{C}$
Rectifier - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1600	V
I_F	$T_s = 25^\circ\text{C}, T_j = 150^\circ\text{C}$		39	A
I_{Fnom}			8	A
I_{FSM}	$t_p = 10\text{ ms}$ $\sin 180^\circ$	$T_j = 25^\circ\text{C}$	220	A
		$T_j = 150^\circ\text{C}$	200	A
I^2t	$t_p = 10\text{ ms}$ $\sin 180^\circ$	$T_j = 25^\circ\text{C}$	242	A^2s
		$T_j = 150^\circ\text{C}$	200	A^2s
T_j			-40 ... 150	$^\circ\text{C}$
Module				
$I_t(\text{RMS})$	$T_{\text{terminal}} = 80^\circ\text{C}, 20\text{ A per spring}$			A
T_{stg}			-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, 1 min		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
$V_{CE(\text{sat})}$	$I_C = 8\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.85	2.10		V
		$T_j = 150^\circ\text{C}$	2.25	2.45		V
V_{CE0}	chiplevel	$T_j = 25^\circ\text{C}$	0.8	0.9		V
		$T_j = 150^\circ\text{C}$	0.7	0.8		V
r_{CE}	$V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	131	150		$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	194	206		$\text{m}\Omega$
$V_{GE(\text{th})}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1\text{ mA}$		5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3		mA
						mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$		0.49		nF
C_{oes}	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		0.05		nF
C_{res}		$f = 1\text{ MHz}$		0.03		nF

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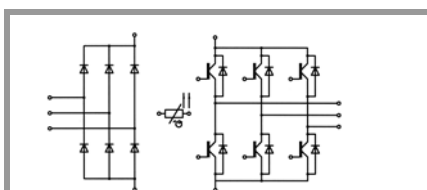
Features

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Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- Temperature sensor: No basic insulation to main circuit, max. potential difference 850V to -DC

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
Q_G	- 8 V...+ 15 V		45		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	32		ns
t_r	$I_C = 8\text{ A}$	$T_j = 150^\circ\text{C}$	34		ns
E_{on}	$R_{G on} = 47\ \Omega$	$T_j = 150^\circ\text{C}$	0.9		mJ
$t_{d(off)}$	$R_{G off} = 47\ \Omega$	$T_j = 150^\circ\text{C}$	295		ns
t_f		$T_j = 150^\circ\text{C}$	68		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	0.7		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8\text{ W/K}^*\text{m}$		1.84		K/W
Inverse - Diode					
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$	2.3	2.7	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$	2.4	2.7	V
	chipelevel				
V_{F0}		$T_j = 25^\circ\text{C}$	1.3	1.5	V
	chipelevel	$T_j = 150^\circ\text{C}$	0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$	129	144	m Ω
	chipelevel	$T_j = 150^\circ\text{C}$	181	198	m Ω
I_{RRM}	$I_F = 8\text{ A}$	$T_j = 150^\circ\text{C}$	7.7		A
Q_{rr}	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$	1.23		μC
	$V_{CC} = 600\text{ V}$				
E_{rr}	$di/dt_{off} = 335\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	0.5		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W/K}^*\text{m}$		2.53		K/W
Rectifier - Diode					
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$	1	1.2	V
	chipelevel	$T_j = 125^\circ\text{C}$	0.9	1.1	V
V_{F0}		$T_j = 25^\circ\text{C}$	0.9	1	V
	chipelevel	$T_j = 125^\circ\text{C}$	0.7	0.8	V
r_F		$T_j = 25^\circ\text{C}$	15	29	m Ω
	chipelevel	$T_j = 125^\circ\text{C}$	21	34	m Ω
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W/K}^*\text{m}$		1.5		K/W
Module					
M_s	to heat sink	2		2.5	Nm
W			20		g
Temperature Sensor					
R_{100}	$T_r = 100^\circ\text{C}$, tolerance = 3 %		1670 \pm 3%		Ω
$R(T)$	$R(T)=1000\Omega[1+A(T-25^\circ\text{C})+B(T-25^\circ\text{C})^2]$ $A = 7.635 \cdot 10^{-3}\text{ }^\circ\text{C}^{-1}$, $B = 1.731 \cdot 10^{-5}\text{ }^\circ\text{C}^{-2}$				



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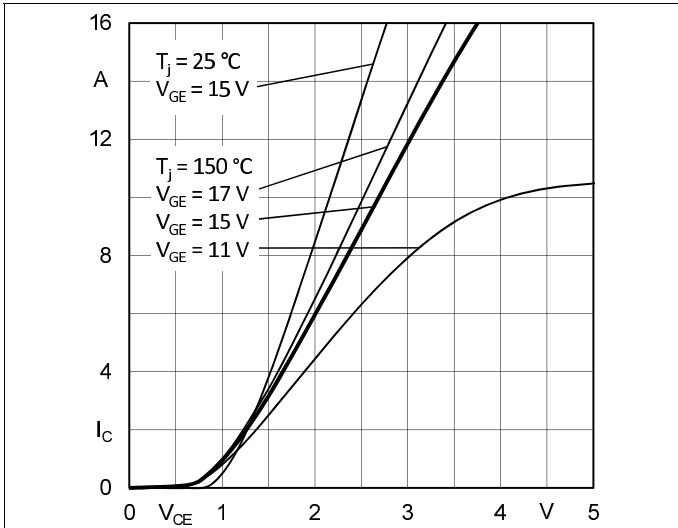


Fig. 1: Typ. output characteristic

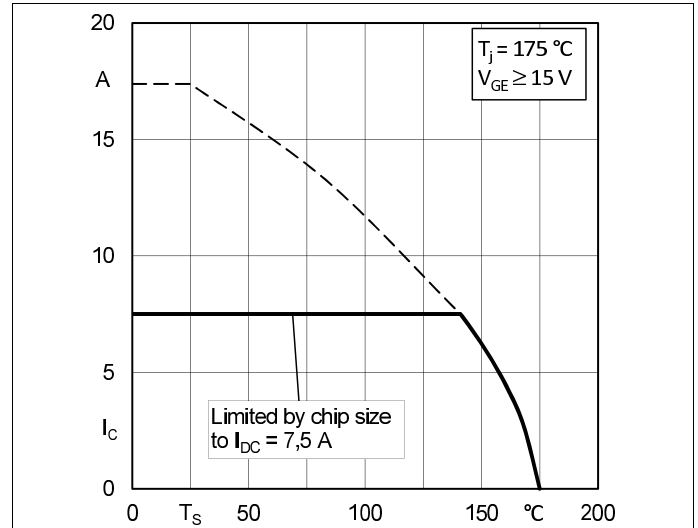


Fig. 2: Typ. rated current vs. temperature $I_C = f(T_s)$

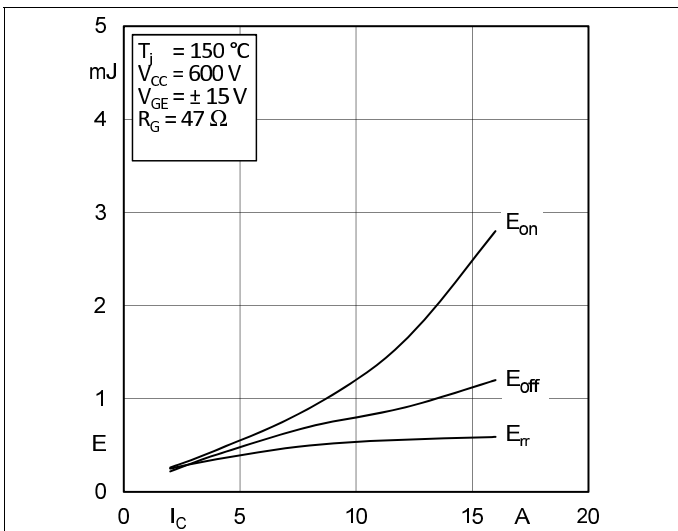


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

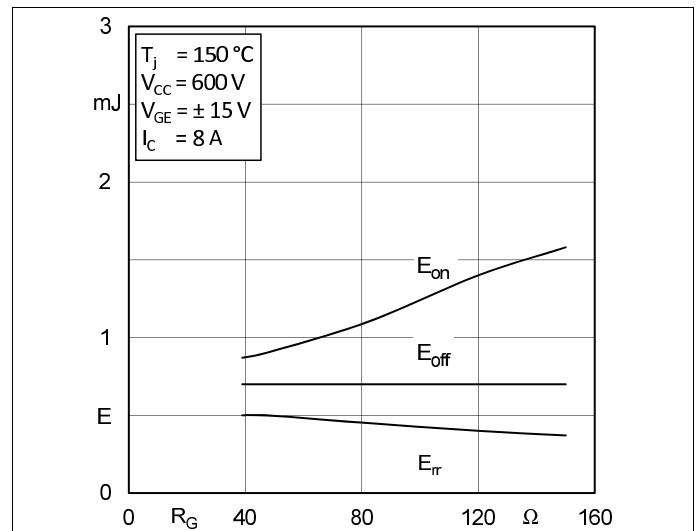


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

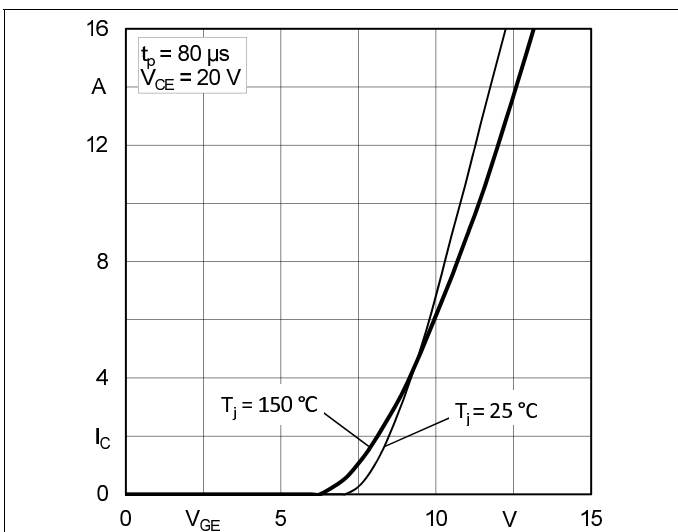


Fig. 5: Typ. transfer characteristic

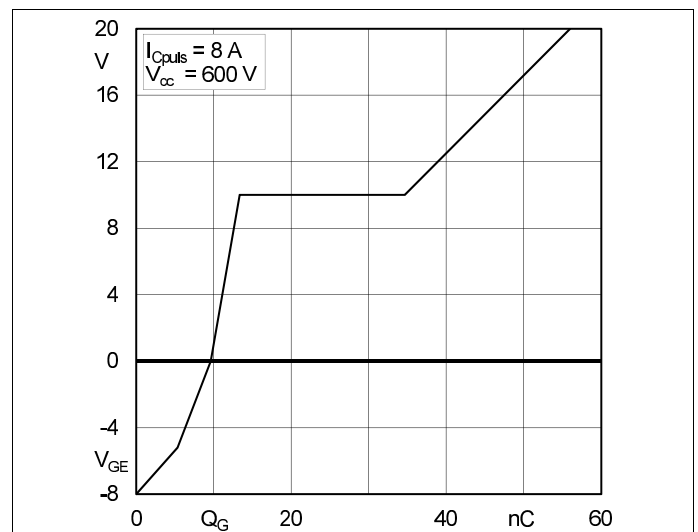


Fig. 6: Typ. gate charge characteristic

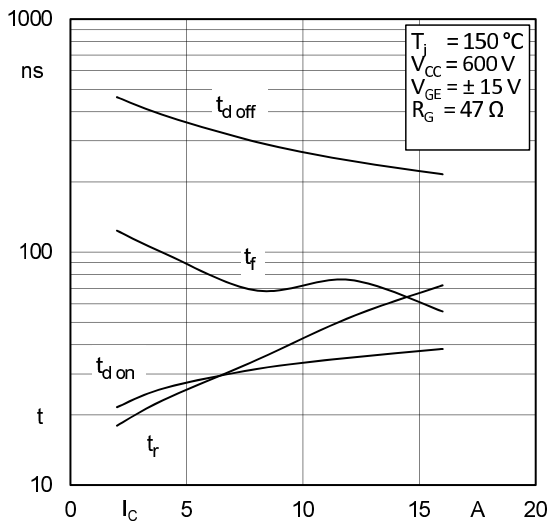


Fig. 7: Typ. switching times vs. I_c

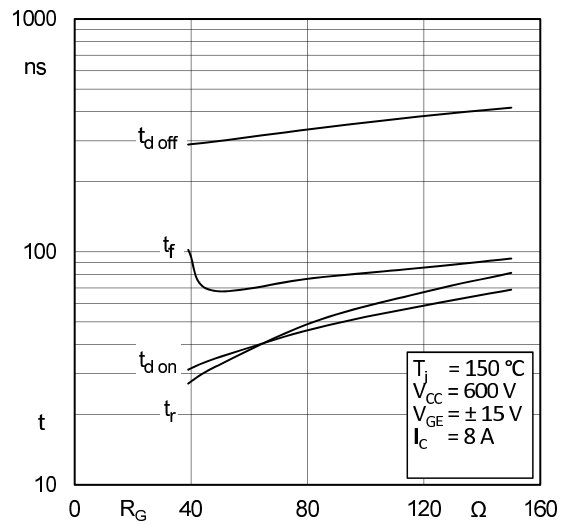


Fig. 8: Typ. switching times vs. gate resistor R_G

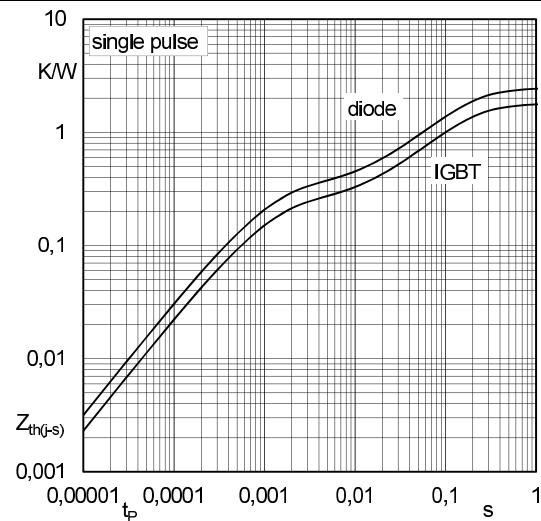


Fig. 9: Transient thermal impedance of IGBT and Diode

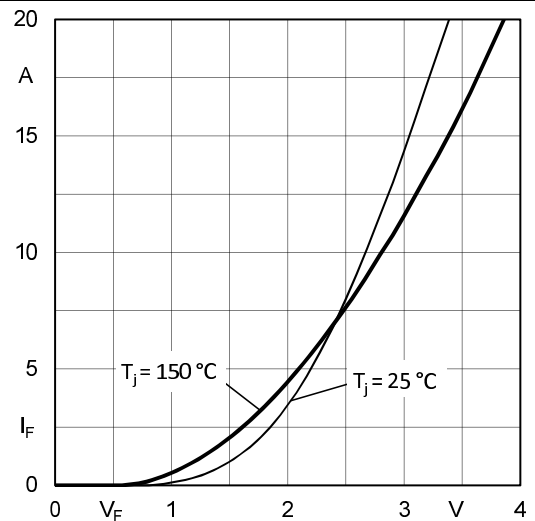


Fig. 10: CAL diode forward characteristic

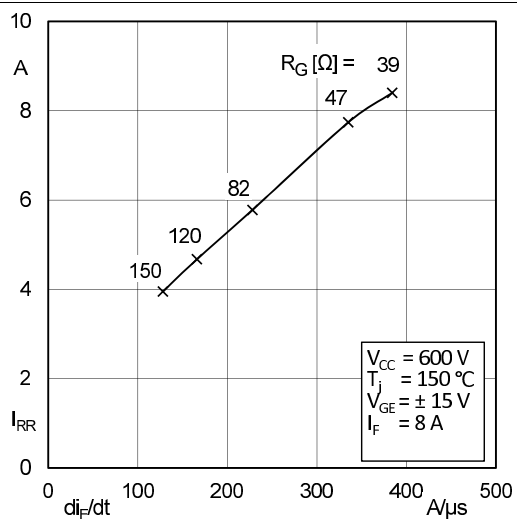


Fig. 11: Typ. CAL diode peak reverse recovery current

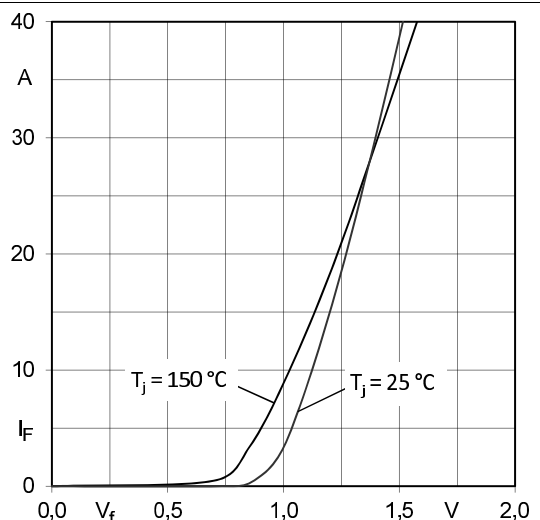


Fig. 12: Typ. input bridge forward characteristic

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